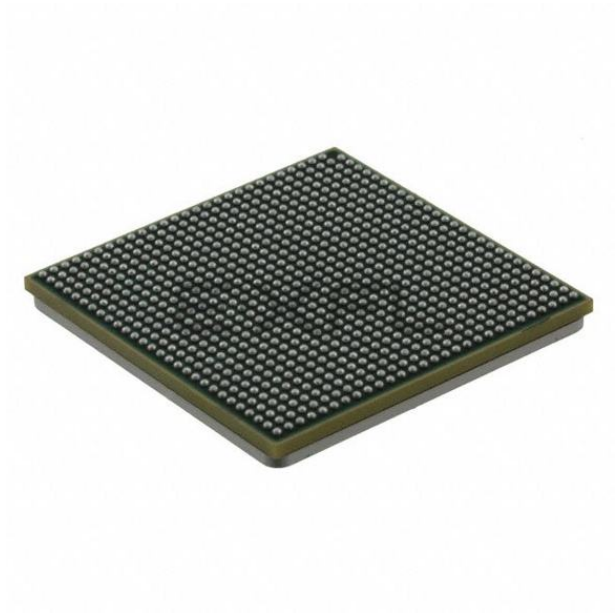


Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	-
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (2)
USB	USB 2.0 (3)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 90°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8536avjaqga

This figure shows the major functional units within the chip.

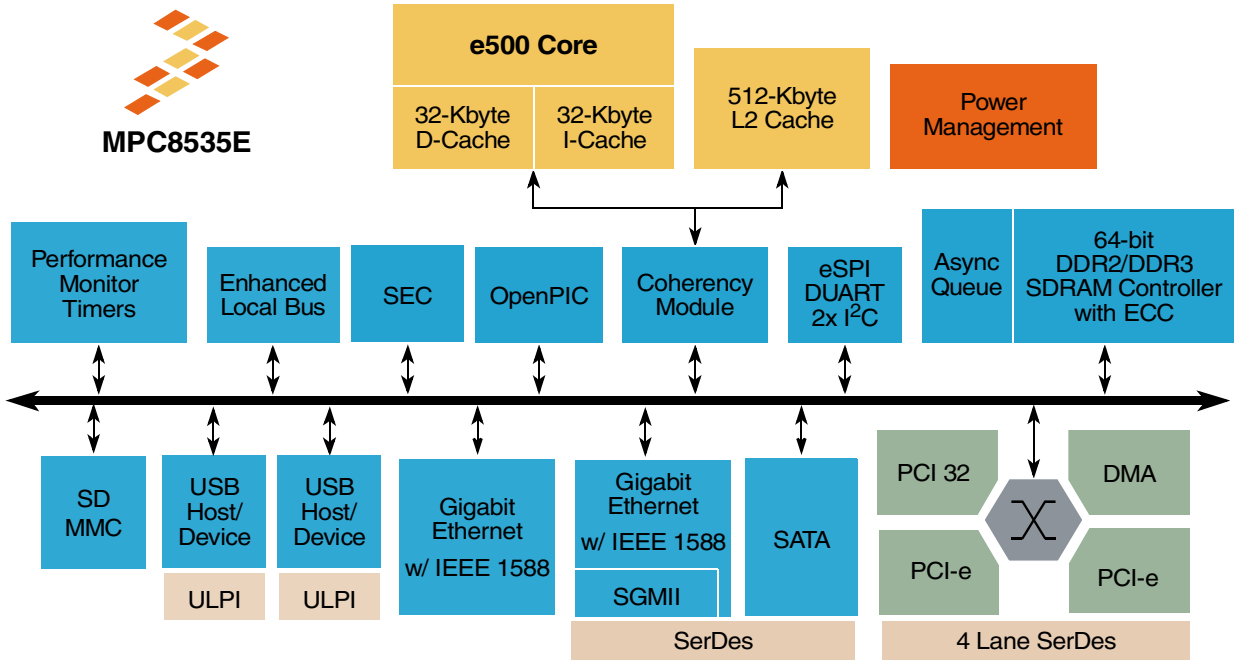


Figure 1. Chip Block Diagram

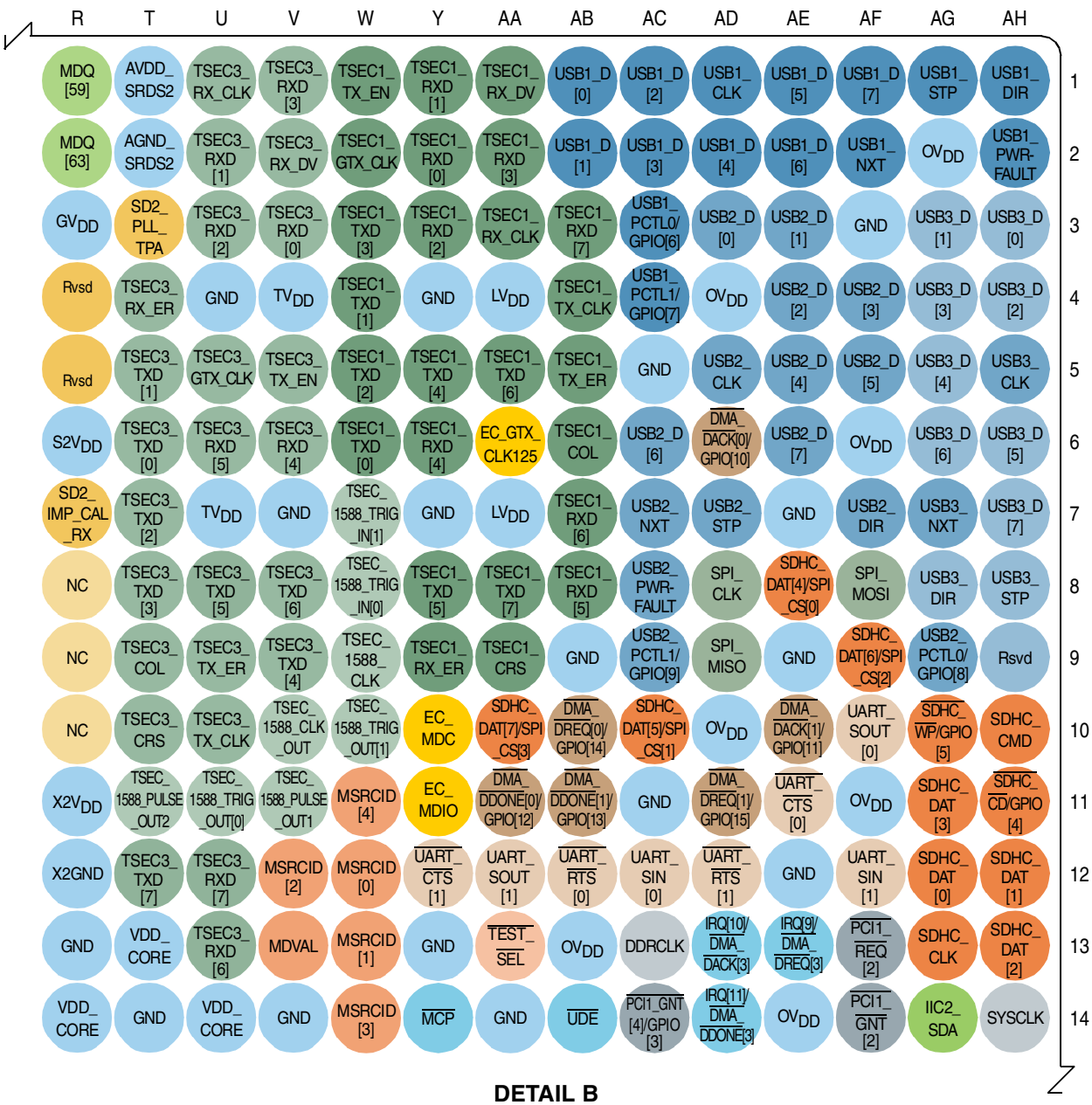
1 Pin Assignments and Reset States

NOTE

The naming convention of TSEC1 and TSEC3 is used to allow the splitting voltage rails for the eTSEC blocks and to ease the port of existing PowerQUICC III software

NOTE

The UART_SOUT[0:1] and $\overline{\text{TEST\_SEL}}$ pins must be set to a proper state during POR configuration. See Table 1 for more details.



DETAIL B

Figure 4. Chip Pin Map Detail B

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
LAD[0:31]	Muxed data / address	K22,L21,L22,K23,K24, L24,L25,K25,L28,L27, K28,K27,J28,H28,H27, G27,G26,F28,F26,F25, E28,E27,E26,F24,E24, C26,G24,E23,G23,F22, G22,G21	I/O	BV_{DD}	5,9,29
LDP[0:3]	Data parity	K26,G28,B27,E25	I/O	BV_{DD}	29
LA[27]	Burst address	L19	O	BV_{DD}	5,9,29
LA[28:31]	Port address	K16,K17,H17,G17	O	BV_{DD}	5,7,9,29
$\overline{\text{LCS}}$[0:4]	Chip selects	K18,G19,H19,H20,G16	O	BV_{DD}	29
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	Chips selects / DMA Request	H16	I/O	BV_{DD}	1,29
$\overline{\text{LCS6}}$/$\overline{\text{DMA\_DACK2}}$	Chips selects / DMA Ack	J16	O	BV_{DD}	1,29
$\overline{\text{LCS7}}$/$\overline{\text{DMA\_DDONE2}}$	Chips selects / DMA Done	L18	O	BV_{DD}	1,29
$\overline{\text{LWE0}}$/$\overline{\text{LBS0}}$/$\overline{\text{LFWE}}$	Write enable / Byte select	J22	O	BV_{DD}	5,9,29
$\overline{\text{LWE[1:3]}}$/$\overline{\text{LBS[1:3]}}$	Write enable / Byte select	H22,H23,H21	O	BV_{DD}	5,9,29
LBCTL	Buffer control	J25	O	BV_{DD}	5,8,9,29
LALE	Address latch enable	J26	O	BV_{DD}	5,8,9,29
LGPL0/LFCLE	UPM general purpose line 0 / FLash command latch enable	J20	O	BV_{DD}	5,9,29
LGPL1/LFALE	UPM general purpose line 1 / Flash address latch enable	K20	O	BV_{DD}	5,9,29
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LFRE}}$	UPM general purpose line 2 / Output enable/Flash read enable	G20	O	BV_{DD}	5,8,9,29
LGPL3/$\overline{\text{LFWP}}$	UPM general purpose line 3 / Flash write protect	H18	O	BV_{DD}	5,9,29
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT /LPBSE/LFRB	UPM general purpose line 4 / Target Ack/Wait/SDRAM parity byte select/Flash Ready-busy	L20	I/O	BV_{DD}	29, 35
LGPL5	UPM general purpose line 5 / Amux	K19	O	BV_{DD}	5,9,29
LCLK[0:2]	Local bus clock	H24,J24,H25	O	BV_{DD}	29
LSYNC_IN	Synchronization	D27	I	BV_{DD}	29
LSYNC_OUT	Local bus DLL	D28	O	BV_{DD}	29
DMA					
$\overline{\text{DMA\_DACK}}$[0:1] /GPIO[10:11]	DMA Acknowledge	AD6,AE10	O	OV_{DD}	—

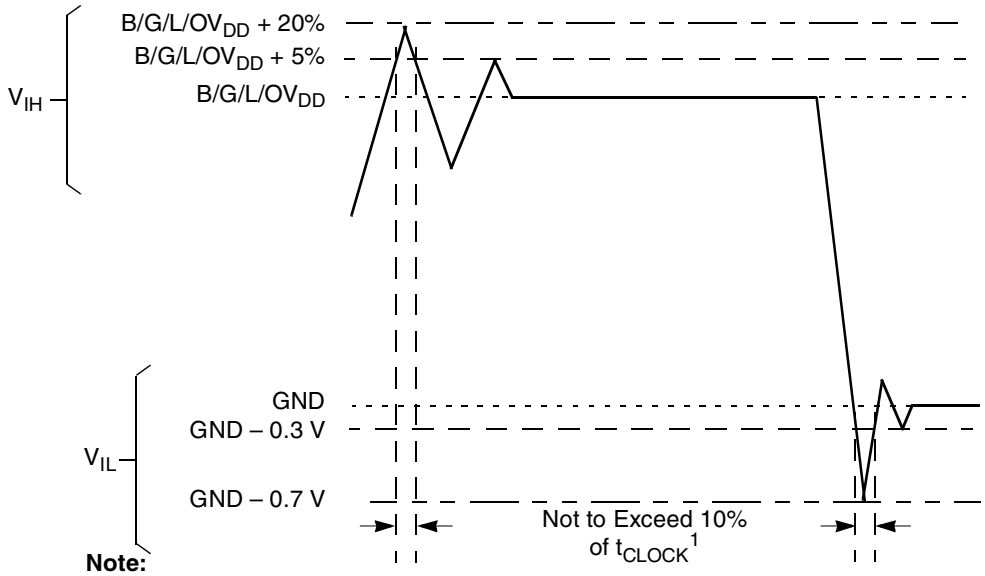
Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
General-Purpose Input/Output					
GPIO[0:1]/PCI1_REQ[3:4]	GPIO/PCI request	Y15,AE15	I/O	OV_{DD}	—
GPIO[2:3]/PCI1_GNT[3:4]	GPIO/PCI grant	AA15,AC14	I/O	OV_{DD}	—
GPIO[4]/SDHC_CD	GPIO/SDHC card detection	AH11	I/O	OV_{DD}	—
GPIO[5]/SDHC_WP	GPIO/SDHC write protection	AG10	I/O	OV_{DD}	32
GPIO[6]/USB1_PCTL0	GPIO/USB1 PCTL0	AC3	I/O	OV_{DD}	—
GPIO[7]/USB1_PCTL1	GPIO/USB1 PCTL1	AC4	I/O	OV_{DD}	—
GPIO[8]/USB2_PCTL0	GPIO/USB2 PCTL0	AG9	I/O	OV_{DD}	—
GPIO[9]/USB2_PCTL1	GPIO/USB2 PCTL1	AC9	I/O	OV_{DD}	—
GPIO[10:11] /DMA_DACK[0:1]	GPIO/DMA Ack	AD6,AE10	I/O	OV_{DD}	—
GPIO[12:13] /DMA_DDONE[0:1]	GPIO/DMA done	AA11,AB11	I/O	OV_{DD}	—
GPIO[14:15] /DMA_DREQ[0:1]	GPIO/DMA request	AB10,AD11	I/O	OV_{DD}	—
System Control					
HRESET	Hard reset	AG16	I	OV_{DD}	—
HRESET_REQ	Hard reset - request	AG15	O	OV_{DD}	22
SRESET	Soft reset	AG19	I	OV_{DD}	—
CKSTP_IN	CheckStop in	AG18	I	OV_{DD}	—
CKSTP_OUT	CheckStop Output	AH17	O	OV_{DD}	2,4
Debug					
TRIG_IN	Trigger in	W19	I	OV_{DD}	—
TRIG_OUT/READY /QUIESCE	Trigger out/Ready/Quiesce	V19	O	OV_{DD}	22
MSRCID[0:1]	Memory debug source port ID	W12,W13	O	OV_{DD}	6,9
MSRCID[2:4]	Memory debug source port ID	V12, W14,W11	O	OV_{DD}	6,9,22
MDVAL	Memory debug data valid	V13	O	OV_{DD}	6,22
CLK_OUT	Clock Out	W15	O	OV_{DD}	11
Clock					
RTC	Real time clock	AF15	I	OV_{DD}	—
SYSCLK	System clock / PCI clock	AH14	I	OV_{DD}	—
DDRCLK	DDR clock	AC13	I	OV_{DD}	30
JTAG					

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
TCK	Test clock	AG28	I	OV_{DD}	—
TDI	Test data in	AH28	I	OV_{DD}	12
TDO	Test data out	AF28	O	OV_{DD}	11
TMS	Test mode select	AH27	I	OV_{DD}	12
$\overline{\text{TRST}}$	Test reset	AH21	I	OV_{DD}	12
DFT					
L1_TSTCLK	L1 test clock	AA21	I	OV_{DD}	19
L2_TSTCLK	L2 test clock	AA20	I	OV_{DD}	19
$\overline{\text{LSSD\_MODE}}$	LSSD Mode	AC25	I	OV_{DD}	19
$\overline{\text{TEST\_SEL}}$	Test select	AA13	I	OV_{DD}	19
Power Management					
ASLEEP	Asleep	AG20	O	OV_{DD}	9,16,22
POWER_OK	Power OK	AC26	I	OV_{DD}	—
POWER_EN	Power enable	AE27	O	OV_{DD}	—
Power and Ground Signals					
OVDD	General I/O supply	Y18,AG2,AD4,AB16, AF6,AC18,AB13,AD10, AE14,AD16,AD25, AF27,AE22,AF11, AF20,AF24	—	OV_{DD}	—
LVDD	GMAC 1 I/O supply	AA7, AA4	Power for TSEC1 interfaces	LV_{DD}	—
TVDD	GMAC 3 I/O supply	V4,U7	Power for TSEC3 interfaces	TV_{DD}	—
GVDD	SSTL2 DDR supply	B1,B11,C7,C9,C14, C17,D4,D6,R3,D15,E2, E8,C24,E18,F5,E14, C21,G3,G7,G9,G11, H5,H12,E22,F15,J10, K3,K12,K14,H14,D20, E11,M1,N5	Power for DDR DRAM I/O	GV_{DD}	—
BVDD	Local bus I/O supply	L23,J18,J23,J19,F20, F23,H26,J21	Power for Local Bus	BV_{DD}	—
SVDD	SerDes 1 core logic supply	M27,N25,P28,R24, R26,T24,T27,U25, W24,W26,Y24,Y27, AA25,AB28,AD27	—	SV_{DD}	—

This figure shows the undershoot and overshoot voltages at the interfaces of the chip.



Note:

1. t_{CLOCK} refers to the clock period associated with the respective interface:
   For I^2C and JTAG, t_{CLOCK} references SYSCLK.
   For DDR, t_{CLOCK} references MCLK.
   For eTSEC, t_{CLOCK} references EC_GTX_CLK125.
   For eLBC, t_{CLOCK} references LCLK.
   For PCI, t_{CLOCK} references PCI1_CLK or SYSCLK.

2. With the PCI overshoot allowed (as specified above), the device does not fully comply with the maximum AC ratings and device protection guideline outlined in the PCI rev. 2.2 standard (section 4.2.2.3).

Figure 7. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}$

The core voltage must always be provided at nominal 1.0 V . (See Table 3 for actual recommended core voltage). Voltage to the processor interface I/Os are provided through separate sets of supply pins and must be provided at the voltages shown in Table 3. The input voltage threshold scales with respect to the associated I/O supply voltage. OV_{DD} and LV_{DD} based receivers are simple CMOS I/O circuits and satisfy appropriate LVCMOS type specifications. The DDR2 and DDR3 SDRAM interface uses differential receivers referenced by the externally supplied MVREF*n* signal (nominally set to GVDD/2) as is appropriate for the SSTL_1.8 electrical signaling standard for DDR2 or 1.5-V electrical signaling for DDR3. The DDR DQS receivers cannot be operated in single-ended fashion. The complement signal must be properly driven and cannot be grounded.

2.1.3 Output Driver Characteristics

This table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 4. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 35	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	1
	45(default) 45(default) 125	BV_{DD} = 3.3 V BV_{DD} = 2.5 V BV_{DD} = 1.8 V	
PCI signals	25	OV_{DD} = 3.3 V	2
	42 (default)		
DDR2 signal	16 32 (half strength mode)	GV_{DD} = 1.8 V	3
DDR3 signal	20 40 (half strength mode)	GV_{DD} = 1.5 V	2
TSEC signals	42	LV_{DD} = 2.5/3.3 V	—
DUART, system control, JTAG	42	OV_{DD} = 3.3 V	—
I^2C	150	OV_{DD} = 3.3 V	—

Notes:

1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI1\_GNT1}}$ signal at reset.
3. The drive strength of the DDR2 or DDR3 interface in half-strength mode is at T_j = 105°C and at GV_{DD} (min)

2.2 Power Sequencing

The chip requires its power rails to be applied in a specific sequence in order to ensure proper chip operation. These requirements are as follows for power up:

1. V_{DD_PLAT}, V_{DD_CORE} (if POWER_EN is not used to control V_{DD_CORE}), AV_{DD}, BV_{DD}, LV_{DD}, OV_{DD}, SV_{DD},$S2V_{DD}$, TV_{DD}, XV_{DD} and $X2V_{DD}$
2. [Wait for POWER_EN to assert], then V_{DD_CORE} (if POWER_EN is used to control V_{DD_CORE})
3. GV_{DD}

All supplies must be at their stable values within 50 ms.

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

From a system standpoint, if any of the I/O power supplies ramp prior to the VDD platform supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-up, and extra current may be drawn by the chip.

During the Deep Sleep state, the VDD core supply is removed. But all other power supplies remain applied. Therefore, there is no requirement to apply the VDD core supply before any other power rails when the silicon waking from Deep Sleep.

This table provides the DDR capacitance when GV_{DD}(type) = 1.8 V.

Table 14. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1, 2
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1, 2

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V (for DDR2), f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.
2. This parameter is sampled. GV_{DD} = 1.5 V ± 0.075 V (for DDR3), f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.175 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition		Symbol	Min	Max	Unit	Note
Current draw for $MV_{REF}n$	DDR2 SDRAM	I_{MVREFn}	—	1500	μA	1
	DDR3 SDRAM			1250		

1.The voltage regulator for MV_{REF} must be able to supply up to 1500 μA or 1250 uA current for DDR2 or DDR3 respectively.

2.6.2 DDR2 and DDR3 SDRAM Interface AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM Controller interface. The DDR controller supports both DDR2 and DDR3 memories. Please note that although the minimum data rate for most off-the-shelf DDR3 DIMMs available is 800 MHz, JEDEC specification does allow the DDR3 to run at the data rate as low as 606 MHz. Unless otherwise specified, the AC timing specifications described in this section for DDR3 is applicable for data rate between 606 MHz and 667 MHz, as long as the DC and AC specifications of the DDR3 memory to be used are compliant to both JEDEC specifications as well as the specifications and requirements described in this document.

2.6.2.1 DDR2 and DDR3 SDRAM Interface Input AC Timing Specifications

These tables provide the input AC timing specifications for the DDR controller.

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 V ± 5%

Parameter		Symbol	Min	Max	Unit
AC input low voltage	667	V_{ILAC}	—	MV_{REF} – 0.20	V
	<=533		—	MV_{REF} – 0.25	V
AC input high voltage	667	V_{IHAC}	MV_{REF} + 0.20	—	V
	<=533		MV_{REF} + 0.25	—	V

2.6.2.2 DDR2 and DDR3 SDRAM Interface Output AC Timing Specifications

This table contains the output AC timing targets for the DDR2 and DDR3 SDRAM interface.

Table 19. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8 V ± 5% for DDR2 or 1.5 V ± 5% for DDR3.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MCK[n] cycle time, MCK[n]/$\overline{\text{MCK}}$[n] crossing	t_{MCK}	3.0	5	ns	2
ADDR/CMD output setup with respect to MCK	t_{DDKHAS}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
ADDR/CMD output hold with respect to MCK	t_{DDKHAX}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
$\overline{\text{MCS}}$[n] output setup with respect to MCK	t_{DDKHCS}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
$\overline{\text{MCS}}$[n] output hold with respect to MCK	t_{DDKHCX}			ns	3
667 MHz		1.10	—		7
533 MHz		1.48	—		
400 MHz		1.95	—		
MCK to MDQS Skew	t_{DDKHMH}			ns	4
<= 667 MHz		–0.6	0.6		7
MDQ/MECC/MDM output setup with respect to MDQS	t_{DDKHDS}, t_{DDKLDS}			ps	5
667 MHz		450	—		7
533 MHz		538	—		
400 MHz		700	—		
MDQ/MECC/MDM output hold with respect to MDQS	t_{DDKHDX}, t_{DDKLDX}			ps	5
667 MHz		450	—		7
533 MHz		538	—		
400 MHz		700	—		
MDQS preamble start	t_{DDKHMP}			ns	6

Table 19. DDR SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of 1.8 V ± 5% for DDR2 or 1.5 V ± 5% for DDR3.

Parameter	Symbol [1]	Min	Max	Unit	Notes
<= 667 MHz		$0.9 \times t_{MCK}$			7
MDQS epilogue end	t_{DDKHME}			ns	6
<= 667 MHz		$0.4 \times t_{MCK}$	$0.6 \times t_{MCK}$		7

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8536E PowerQUICC III Integrated Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.
7. Maximum DDR2 and DDR3 frequency is 667 MHz

NOTE

For the ADDR/CMD setup and hold specifications in Table 19, it is assumed that the Clock Control register is set to adjust the memory clocks by 1/2 applied cycle.

Table 25. RGMII, RTBI, and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.37	2.63	V	1,2
Output high voltage (LV_{DD}/TV_{DD} = Min, IOH = –1.0 mA)	V_{OH}	2.00	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	GND – 0.3	0.40	V	—
Input high voltage	V_{IH}	1.70	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.70	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	10	µA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–15	—	µA	3

Note:

1 LV_{DD} supports eTSECs 1.

2 TV_{DD} supports eTSECs 3.

3 Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

2.9.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI are presented in this section.

2.9.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, since they have similar performance and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSEC*n*'s TSEC*n*_TX_CLK, while the receive clock must be applied to pin TSEC*n*_RX_CLK. The eTSEC internally uses the transmit clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back out onto the TSEC*n*_GTX_CLK pin (while transmit data appears on TSEC*n*_TXD[7:0], for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSEC*n*_GTX_CLK as a source-synchronous timing reference. Typically, the clock edge that launched the data can be used, since the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is relationship between the maximum FIFO speed and the platform speed. For more information see Section 2.4.6, "Platform to FIFO Restrictions."

A summary of the FIFO AC specifications appears in the following tables.

Table 26. FIFO Mode Transmit AC Timing Specification

Parameter/Condition	Symbol	Min	Typ	Max	Unit
TX_CLK, GTX_CLK clock period[2]	t_{FIT}	6.0	8.0	100	ns
TX_CLK, GTX_CLK duty cycle	t_{FITH}	45	50	55	%
TX_CLK, GTX_CLK peak-to-peak jitter	t_{FITJ}	—	—	250	ps

Table 40. SGMII DC Receiver Electrical Characteristics (continued)

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Receiver differential input impedance	Z_{RX_DIFF}	80	100	120	Ω	—
Receiver common mode input impedance	Z_{RX_CM}	20	—	35	Ω	—
Common mode input voltage	V_{CM}	—	$V_{xcorevss}$	—	V	6

Notes:
1. Input must be externally AC-coupled.
2. $V_{RX\_DIFFp\text{-}p}$ is also referred to as peak to peak input differential voltage
3. The concept of this parameter is equivalent to the Electrical Idle Detect Threshold parameter in PCI Express. See Table 72 for further explanation.
4. The LSTS shown in the table refers to the LSTSA or LSTSE bit field of chip's SerDes 2 control register.
5. $V_{CM\_ACp\text{-}p}$ is also referred to as peak to peak AC common mode voltage.
6. On-chip termination to S2GND (xcorevss).

2.9.3.4 SGMII AC Timing Specifications

This section describes the SGMII transmit and receive AC timing specifications. Transmitter and receiver characteristics are measured at the transmitter outputs (SD2_TX[n] and $\overline{\text{SD2\_TX}}$[n]) or at the receiver inputs (SD2_RX[n] and $\overline{\text{SD2\_RX}}$[n]) as depicted in Figure 32 respectively.

2.9.3.4.1 SGMII Transmit AC Timing Specifications

This table provides the SGMII transmit AC timing targets. A source synchronous clock is not provided.

Table 41. SGMII Transmit AC Timing Specifications

At recommended operating conditions with $X2V_{DD}$ = 1.0V ± 5%.

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Deterministic Jitter	JD	—	—	0.17	UI p-p	—
Total Jitter	JT	—	—	0.35	UI p-p	—
Unit Interval	UI	799.92	800	800.08	ps	1
V_{OD} fall time (80%-20%)	tfall	50	—	120	ps	—
V_{OD} rise time (20%-80%)	t_{rise}	50	—	120	ps	—

Notes:
1. Each UI is 800 ps ± 100 ppm.

Table 53. Local Bus General Timing Parameters (BV_{DD} = 1.8 V DC) (continued)

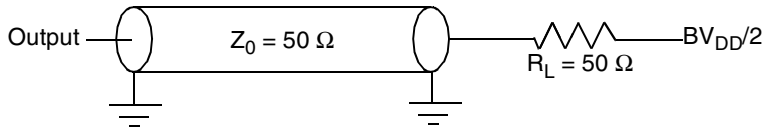
Parameter	Configuration	Symbol [1]	Min	Max	Unit	Notes
Output hold from local bus clock for LAD/LDP	—	$t_{LBKHOX2}$	0.9	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	—	$t_{LBKHOZ1}$	—	2.6	ns	5
Local bus clock to output high impedance for LAD/LDP	—	$t_{LBKHOZ2}$	—	2.6	ns	5

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 1.8-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is guaranteed with LBCR[AHD] = 0.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.

This figure provides the AC test load for the local bus.

Figure 38. Local Bus AC Test Load



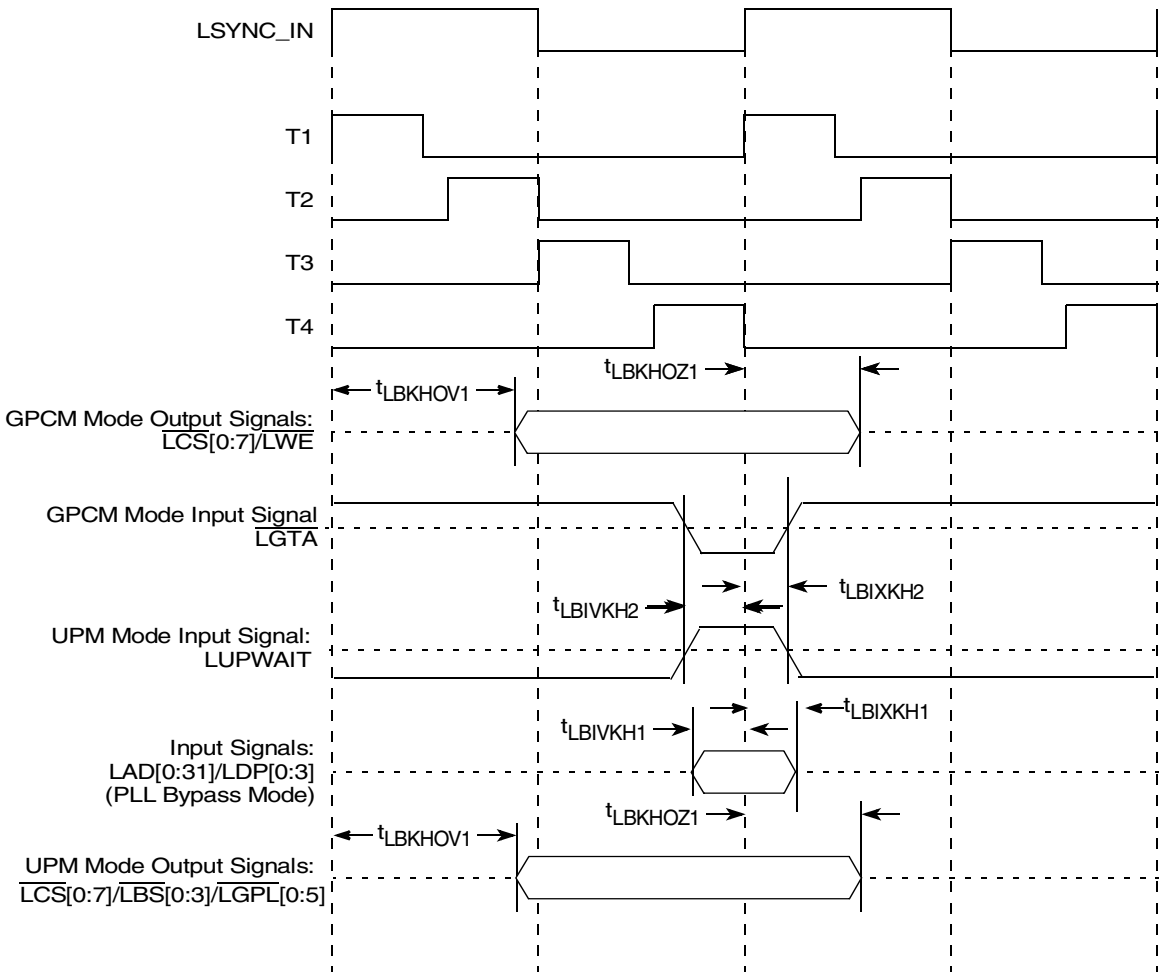


Figure 42. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 8 or 16(PLL Enabled)

2.13 Enhanced Secure Digital Host Controller (eSDHC)

This section describes the DC and AC electrical specifications for the eSDHC interface of the chip.

2.13.1 eSDHC DC Electrical Characteristics

This table provides the DC electrical characteristics for the eSDHC interface of the chip.

Table 55. eSDHC interface DC Electrical Characteristics

At recommended operating conditions (see Table 3)

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Input high voltage	V_{IH}	—	0.625 * OVDD	OVDD+0.3	V	—
Input low voltage	V_{IL}	—	–0.3	0.25 * OVDD	V	—
Input/Output leakage current	I_{IN}/I_{OZ}	—	–10	10	uA	—
Output high voltage	V_{OH}	I_{OH} = -100 uA @OVDDmin	0.75 * OVDD	—	V	—

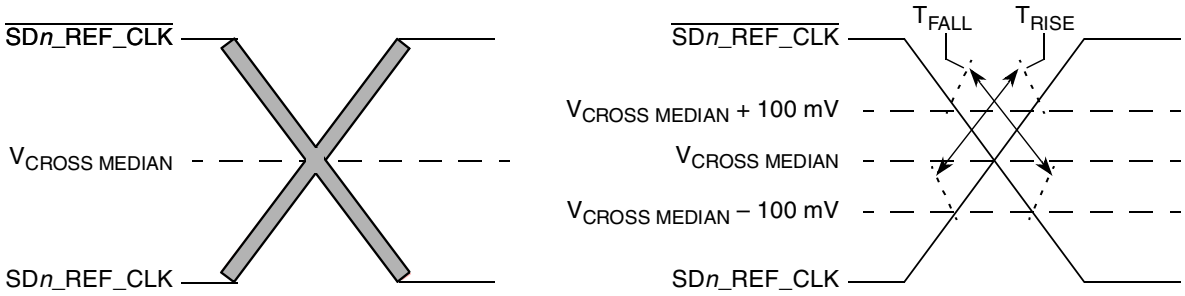


Figure 67. Single-Ended Measurement Points for Rise and Fall Time Matching

The other detailed AC requirements of the SerDes Reference Clocks is defined by each interface protocol based on application usage. See the following sections for detailed information:

- Section 2.9.3.2, "AC Requirements for SGMII SD2_REF_CLK and SD2_REF_CLK"
- Section 2.21.2, "AC Requirements for PCI Express SerDes Clocks"

2.20.2.4.1 Spread Spectrum Clock

SD1_REF_CLK/$\overline{\text{SD1\_REF\_CLK}}$ were designed to work with a spread spectrum clock (+0 to -0.5% spreading at 30–33 kHz rate is allowed), assuming both ends have same reference clock. For better results, a source without significant unintended modulation should be used.

SD2_REF_CLK/$\overline{\text{SD2\_REF\_CLK}}$ are not intended to be used with, and should not be clocked by, a spread spectrum clock source.

2.20.3 SerDes Transmitter and Receiver Reference Circuits

This figure shows the reference circuits for SerDes data lane's transmitter and receiver.

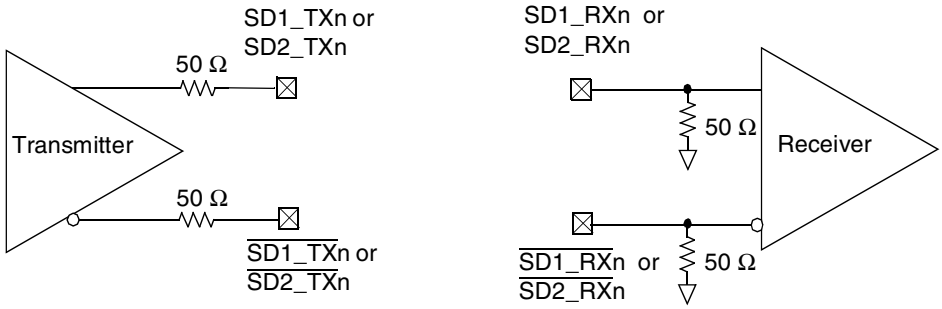


Figure 68. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in each interface protocol section below (PCI Express, SATA or SGMII) in this document based on the application usage:

- Section 2.9.3, "SGMII Interface Electrical Characteristics"
- Section 2.21, "PCI Express"
- Section 2.16, "Serial ATA (SATA)"

Please note that external AC Coupling capacitor is required for the above three serial transmission protocols with the capacitor value defined in specification of each protocol section.

Table 79. Package Thermal Characteristics (continued)

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Junction-to-ambient (@200 ft/min)	Four layer board (2s2p)	$R_{\theta JA}$	14	°C/W	1, 2
Junction-to-board thermal	—	$R_{\theta JB}$	10	°C/W	3
Junction-to-case thermal	—	$R_{\theta JC}$	< 0.1	°C/W	4

Notes

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 and JESD51-6 with the board (JESD51-9) horizontal.
3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the active surface of the die and the case top surface determined by the cold plate method (MIL SPEC-883 Method 1012.1) with the calculated case temperature. Actual thermal resistance is less than 0.1 •C/W

Simulations with heat sinks were done with the package mounted on the 2s2p thermal test board. The thermal interface material was a typical thermal grease such as Dow Corning 340 or Wakefield 120 grease.For system thermal modeling, the chip's thermal model without a lid is shown in Figure 72 The substrate is modeled as a block 29 x 29 x 1.2 mm with an in-plane conductivity of 19.8 W/m•K and a through-plane conductivity of 1.13 W/m•K. The solder balls and air are modeled as a single block 29 x 29 x 0.5 mm with an in-plane conductivity of 0.034 W/m•K and a through plane conductivity of 12.1 W/m•K. The die is modeled as 9.6 x 9.57 mm with a thickness of 0.75 mm. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate assuming a conductivity of 7.5 W/m•K in the thickness dimension of 0.07 mm. The die is centered on the substrate. The thermal model uses approximate dimensions to reduce grid. Please refer to the case outline for actual dimensions.

2.24.2 Recommended Thermal Model

This table shows the chip's thermal model.

Table 80. Thermal Model

Conductivity	Value	Units
Die (9.6x9.6 × 0.85 mm)		
Silicon	Temperature dependent	—
Bump/Underfill (9.6 x 9.6 × 0.07 mm) Collapsed Thermal Resistance		
Kz	7.5	W/m•K
Substrate (29 × 29 × 1.2 mm)		
Kx	19.8	W/m•K
Ky	19.8	
Kz	1.13	
Solder and Air (29 × 29 × 0.5 mm)		
Kx	0.034	W/m•K
Ky	0.034	
Kz	12.1	

These capacitors should have a value of 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON). However, customers should work directly with their power regulator vendor for best values types and quantity of bulk capacitors.

3.5 SerDes Block Power Supply Decoupling Recommendations

he SerDes1 and SerDes2 blocks require a clean, tightly regulated source of power (SnV_{DD} and XnV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

- First, the board should have at least 10 x 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the chip. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the chip as close to the supply and ground connections as possible.
- Second, there should be a 1-µF ceramic chip capacitor from each SerDes supply (SnV_{DD} and XnV_{DD}) to the board ground plane on each side of the chip. This should be done for all SerDes supplies.
- Third, between the chip and any SerDes voltage regulator there should be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

3.6 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. All unused active low inputs should be tied to $V_{DD,}TV_{DD}$, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} as required. All unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected. Power and ground connections must be made to all external $V_{DD,}TV_{DD}$, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} and GND pins of the chip.

3.7 Pull-Up and Pull-Down Resistor Requirements

The chip requires weak pull-up resistors (2–10 kΩ is recommended) on open drain type pins including I^2C pins and MPIC interrupt pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 78. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion will give unpredictable results.

The following pins must NOT be pulled down during power-on reset: TSEC1_TXD[3], $\overline{\text{HRESET\_REQ}}$, TRIG_OUT/READY/$\overline{\text{QUIESCE}}$, MSRCID[2:4], ASLEEP. The UART_SOUT[0:1] and $\overline{\text{TEST\_SEL}}$ pins must be set to a proper state during POR configuration. Please refer to the pinlist table (see Table 62) of the individual chip for more details.

See the PCI 2.2 specification for all pull-ups required for PCI.

3.8 Output Buffer DC Impedance

The chip drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 77). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

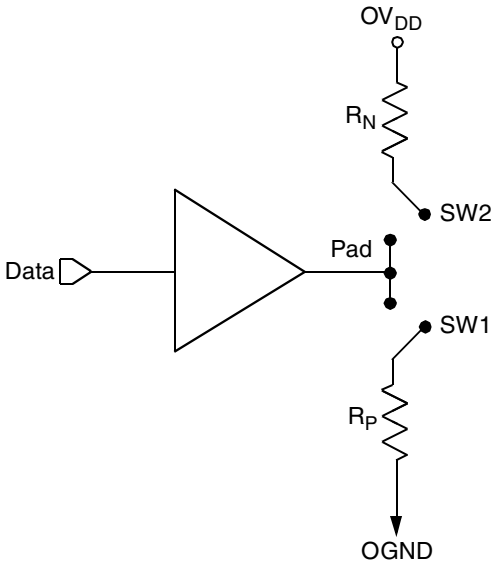


Figure 77. Driver Impedance Measurement

This table summarizes the signal impedance targets. The driver impedances are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 81. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R_N	45 Target	45 Target (cfg_pci_impd=1) 25 Target (cfg_pci_impd=0)	18 Target (full strength mode) 36 Target (full strength mode)	Z_0	Ω
R_P	45 Target	45 Target (cfg_pci_impd=1) 25 Target (cfg_pci_impd=0)	18 Target (full strength mode) 36 Target (full strength mode)	Z_0	Ω

Note: Nominal supply voltages. See Table 1.

3.9 Configuration Pin Muxing

The chip provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Most of these sampled configuration pins are equipped with an on-chip gated resistor of approximately 20 kΩ. This value should permit the 4.7-kΩ resistor to pull the configuration pin to a valid logic low level. The pull-up resistor is enabled only during $\overline{\text{HRESET}}$ (and for platform /system clocks after $\overline{\text{HRESET}}$ deassertion to ensure capture of the reset value). When the input receiver is disabled the pull-up is also, thus allowing functional operation of the pin as an output with minimal signal quality or delay disruption. The default value for all configuration bits treated this way has been encoded such that a high voltage level puts the chip into the default state and external resistors are needed only when non-default settings are required by the user.

The following pins must be connected to XGND if not used:

- SD1_RX[7:4]
- $\overline{\text{SD1\_RX[7:4]}}$
- SD1_REF_CLK
- $\overline{\text{SD1\_REF\_CLK}}$

3.11.3 SerDes 2 Interface Entirely Unused

If the high-speed SerDes 2 interface (SGMII/ SATA) is not used at all, the unused pin should be terminated as described in this section. There are several Reserved pins that need to be either left floating or connected to X2GND. See SerDes2 in Table 1Table 1 for details.

The following pins must be left unconnected (float):

- SD2_TX[0]
- $\overline{\text{SD2\_TX[0]}}$
- Reserved pins L8, L9

The following pins must be connected to X2GND:

- SD2_RX[0]
- $\overline{\text{SD2\_RX[0]}}$
- SD2_REF_CLK
- $\overline{\text{SD2\_REF\_CLK}}$

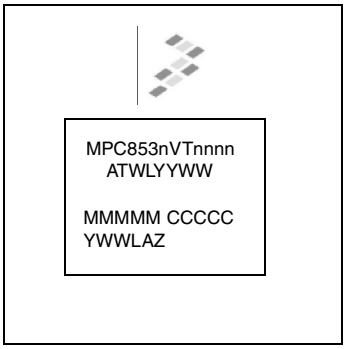
The POR configuration pin cfg_srds2_prtcl[0:2] on TSEC1_TXD[2], TSEC3_TXD[2], TSEC_1588_PUSLE_OUT1 can be used to power down SerDes 2 block for power saving. Note that both S2VDD and X2VDD must remain powered.

4 Ordering Information

Ordering information for the parts fully covered by this specification document is provided in Section 4.1, “Part Numbers Fully Addressed by this Document.”

4.2 Part Marking

Parts are marked as in the example shown in the following figure.



FC-PBGA

Notes:

MMMMM is the 5-digit mask number.
ATWLYYWW is the traceability code.
CCCCC is the country of assembly. This space is left blank if parts are assembled in the United States.

Figure 80. Part Marking for FC-PBGA

4.3 Part Numbering

These tables list all part numbers that are offered for the chip.

Table 83. MPC8535 Part Numbers Commercial Tier

Core/Platform/ DDR (MHz)	Standard Temp Without Security	Standard Temp With Security	Notes
600/400/400	MPC8535AVTAKG(A)	MPC8535EAVTAKG(A)	—
800/400/400	MPC8535AVTANG(A)	MPC8535EAVTANG(A)	—
1000/400/400	MPC8535AVTAQG(A)	MPC8535EAVTAQG(A)	—
1250/500/500	MPC8535AVTATH(A)	MPC8535EAVTATH(A)	—
1250/500/667	MPC8535AVTATLA	MPC8535EAVTATLA	—

Table 84. MPC8535 Part Numbers Industrial Tier

Core/Platform/ DDR (MHz)	Standard Temp Without Security	Standard Temp With Security	Extended Temp Without Security	Extended Temp With Security	Notes
600/400/400	MPC8535BVTAKG(A)	MPC8535EBVTAKG(A)	MPC8535CVTAKG(A)	MPC8535ECVTAKG(A)	1
800/400/400	MPC8535BVTANG(A)	MPC8535EBVTANG(A)	MPC8535CVTANG(A)	MPC8535ECVTANG(A)	
1000/400/400	MPC8535BVTAQG(A)	MPC8535EBVTAQG(A)	MPC8535CVTAQG(A)	MPC8535ECVTAQG(A)	
1250/500/500	MPC8535BVTATH(A)	MPC8535EBVTATH(A)	MPC8535CVTATH(A)	MPC8535ECVTATH(A)	
1250/500/667	MPC8535BVTATLA	MPC8535EBVTATLA	MPC8535CVTATLA	MPC8535ECVTATLA	

Note:

1. The last letter A indicates a Rev 1.2 silicon. It would be Rev 1.0 or Rev 1.1 silicon without a letter A